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	Solidic for form 14400 10			Application Number	10/576,345	
l IN	NFORMATION	I DI	SCLOSURE	Filing Date	April 18, 2006	
	TATEMENT E		_	First Named Inventor	MARCHAND, Gilles	
	TAILMENT L	<i>,</i> ,		Art Unit	TBA	
	(use as many sheets as necessary)			Examiner Name	ТВА	
Sheet	1	of	1	Attorney Docket Number	10404.039.00-US	

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